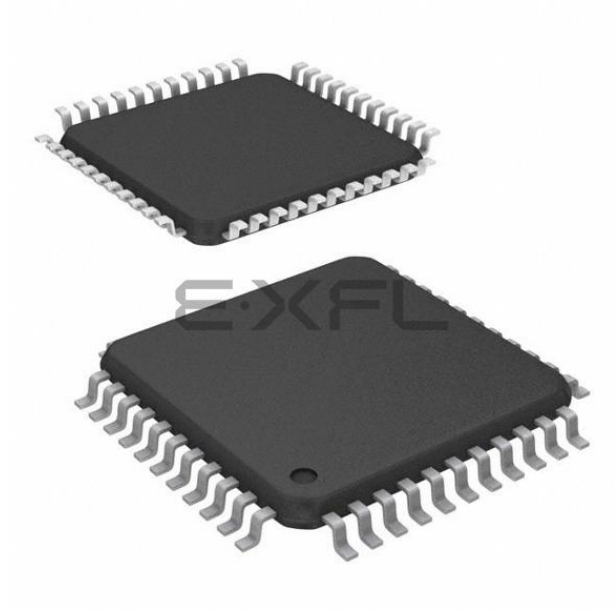

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I²C, IrDA, LINbus, Microwire, SmartCard, SPI, SSP, UART/USART
Peripherals	Brown-out Detect/Reset, CapSense, LCD, POR, PWM, WDT
Number of I/O	36
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 16x10b Slope, 16x12b SAR; D/A 2xIDAC
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-TQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c4126axi-s433

Contents

Functional Definition

CPU and Memory Subsystem

CPU

The Cortex-M0+ CPU in the PSoC 4100S is part of the 32-bit MCU subsystem, which is optimized for low-power operation with extensive clock gating. Most instructions are 16 bits in length and the CPU executes a subset of the Thumb-2 instruction set. It includes a nested vectored interrupt controller (NVIC) block with eight interrupt inputs and also includes a Wakeup Interrupt Controller (WIC). The WIC can wake the processor from Deep Sleep mode, allowing power to be switched off to the main processor when the chip is in Deep Sleep mode.

The CPU also includes a debug interface, the serial wire debug (SWD) interface, which is a two-wire form of JTAG. The debug configuration used for PSoC 4100S has four breakpoint (address) comparators and two watchpoint (data) comparators.

Flash

The PSoC 4100S device has a flash module with a flash accelerator, tightly coupled to the CPU to improve average access times from the flash block. The low-power flash block is designed to deliver two wait-state (WS) access time at 48 MHz. The flash accelerator delivers 85% of single-cycle SRAM access performance on average.

SRAM

Eight KB of SRAM are provided with zero wait-state access at 48 MHz.

SROM

An 8 KB supervisory ROM that contains boot and configuration routines is provided.

System Resources

Power System

The power system is described in detail in the section Power on page 11. It provides assurance that voltage levels are as required for each respective mode and either delays mode entry (for example, on power-on reset (POR)) until voltage levels are as required for proper functionality, or generates resets (for example, on brown-out detection). The PSoC 4100S operates with a single external supply over the range of either 1.8 V ±5% (externally regulated) or 1.8 to 5.5 V (internally regulated) and has three different power modes, transitions between which are managed by the power system. The PSoC 4100S provides Active, Sleep, and Deep Sleep low-power modes.

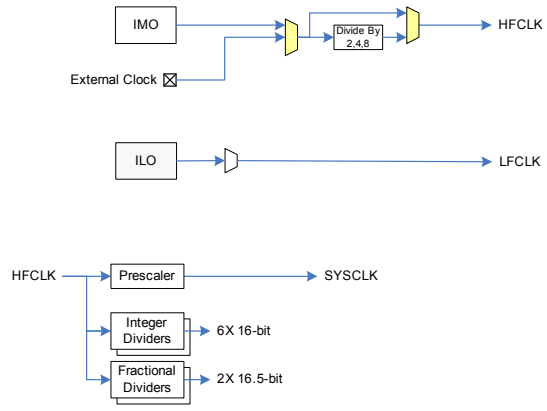
All subsystems are operational in Active mode. The CPU subsystem (CPU, flash, and SRAM) is clock-gated off in Sleep mode, while all peripherals and interrupts are active with instantaneous wake-up on a wake-up event. In Deep Sleep mode, the high-speed clock and associated circuitry is switched off; wake-up from this mode takes 35 µs. The opamps can remain operational in Deep Sleep mode.

Clock System

The PSoC 4100S clock system is responsible for providing clocks to all subsystems that require clocks and for switching between different clock sources without glitching. In addition, the clock system ensures that there are no metastable conditions.

The clock system for the PSoC 4100S consists of the internal main oscillator (IMO), internal low-frequency oscillator (ILO), a 32 kHz Watch Crystal Oscillator (WCO) and provision for an external clock. Clock dividers are provided to generate clocks for peripherals on a fine-grained basis. Fractional dividers are also provided to enable clocking of higher data rates for UARTs.

Figure 2. PSoC 4100S MCU Clocking Architecture



The HFCLK signal can be divided down to generate synchronous clocks for the analog and digital peripherals. There are eight clock dividers for the PSoC 4100S; two of those are fractional dividers. The 16-bit capability allows flexible generation of fine-grained frequency values and is fully supported in PSoC Creator

IMO Clock Source

The IMO is the primary source of internal clocking in the PSoC 4100S. It is trimmed during testing to achieve the specified accuracy.The IMO default frequency is 24 MHz and it can be adjusted from 24 to 48 MHz in steps of 4 MHz. The IMO tolerance with Cypress-provided calibration settings is ±2%.

ILO Clock Source

The ILO is a very low power, nominally 40-kHz oscillator, which is primarily used to generate clocks for the watchdog timer (WDT) and peripheral operation in Deep Sleep mode. ILO-driven counters can be calibrated to the IMO to improve accuracy. Cypress provides a software component, which does the calibration.

Watch Crystal Oscillator (WCO)

The PSoC 4100S clock subsystem also implements a low-frequency (32-kHz watch crystal) oscillator that can be used for precision timing applications.

Watchdog Timer

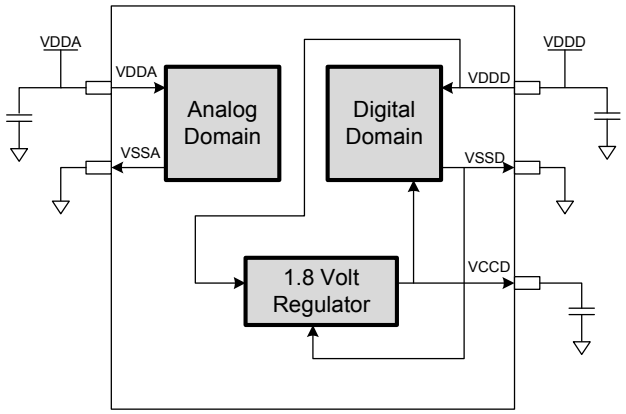
A watchdog timer is implemented in the clock block running from the ILO; this allows watchdog operation during Deep Sleep and generates a watchdog reset if not serviced before the set timeout occurs. The watchdog reset is recorded in a Reset Cause register, which is firmware readable.

Port/Pin	Analog	Smart I/O	Alternate Function 1	Alternate Function 2	Alternate Function 3	Deep Sleep 1	Deep Sleep 2
P2.4	sarmux[4]	prgio[0].io[4]	tcpwm.line[0]:1				scb[1].spi_select1:1
P2.5	sarmux[5]	prgio[0].io[5]	tcpwm.line_compl[0]:1				scb[1].spi_select2:1
P2.6	sarmux[6]	prgio[0].io[6]	tcpwm.line[1]:1				scb[1].spi_select3:1
P2.7	sarmux[7]	prgio[0].io[7]	tcpwm.line_compl[1]:1			lpcomp.comp[0]:1	scb[2].spi_mosi
P3.0		prgio[1].io[0]	tcpwm.line[0]:0	scb[1].uart_rx:1		scb[1].i2c_scl:2	scb[1].spi_mosi:0
P3.1		prgio[1].io[1]	tcpwm.line_compl[0]:0	scb[1].uart_tx:1		scb[1].i2c_sda:2	scb[1].spi_miso:0
P3.2		prgio[1].io[2]	tcpwm.line[1]:0	scb[1].uart_cts:1		cpuss.swd_data	scb[1].spi_clk:0
P3.3		prgio[1].io[3]	tcpwm.line_compl[1]:0	scb[1].uart_rts:1		cpuss.swd_clk	scb[1].spi_select0:0
P3.4		prgio[1].io[4]	tcpwm.line[2]:0		tcpwm.tr_in[6]		scb[1].spi_select1:0
P3.5		prgio[1].io[5]	tcpwm.line_compl[2]:0				scb[1].spi_select2:0
P3.6		prgio[1].io[6]	tcpwm.line[3]:0				scb[1].spi_select3:0
P3.7		prgio[1].io[7]	tcpwm.line_compl[3]:0			lpcomp.comp[1]:1	scb[2].spi_miso
P4.0	csd.vref_ext			scb[0].uart_rx:0		scb[0].i2c_scl:1	scb[0].spi_mosi:0
P4.1	csd.cshieldpads			scb[0].uart_tx:0		scb[0].i2c_sda:1	scb[0].spi_miso:0
P4.2	csd.cmodpad			scb[0].uart_cts:0		lpcomp.comp[0]:0	scb[0].spi_clk:0
P4.3	csd.csh_tank			scb[0].uart_rts:0		lpcomp.comp[1]:0	scb[0].spi_select0:0

Power

The following power system diagram shows the set of power supply pins as implemented for the PSoC 4100S. The system has one regulator in Active mode for the digital circuitry. There is no analog regulator; the analog circuits run directly from the V_{DD} input.

Figure 4. Power Supply Connections



There are two distinct modes of operation. In Mode 1, the supply voltage range is 1.8 V to 5.5 V (unregulated externally; internal regulator operational). In Mode 2, the supply range is1.8 V ±5% (externally regulated; 1.71 to 1.89, internal regulator bypassed).

Mode 1: 1.8 V to 5.5 V External Supply

In this mode, the PSoC 4100S is powered by an external power supply that can be anywhere in the range of 1.8 to 5.5 V. This range is also designed for battery-powered operation. For example, the chip can be powered from a battery system that starts at 3.5 V and works down to 1.8 V. In this mode, the internal regulator of the PSoC 4100S supplies the internal logic and its output is connected to the V_{CCD} pin. The VCCD pin must be bypassed to ground via an external capacitor (0.1 µF; X5R ceramic or better) and must not be connected to anything else.

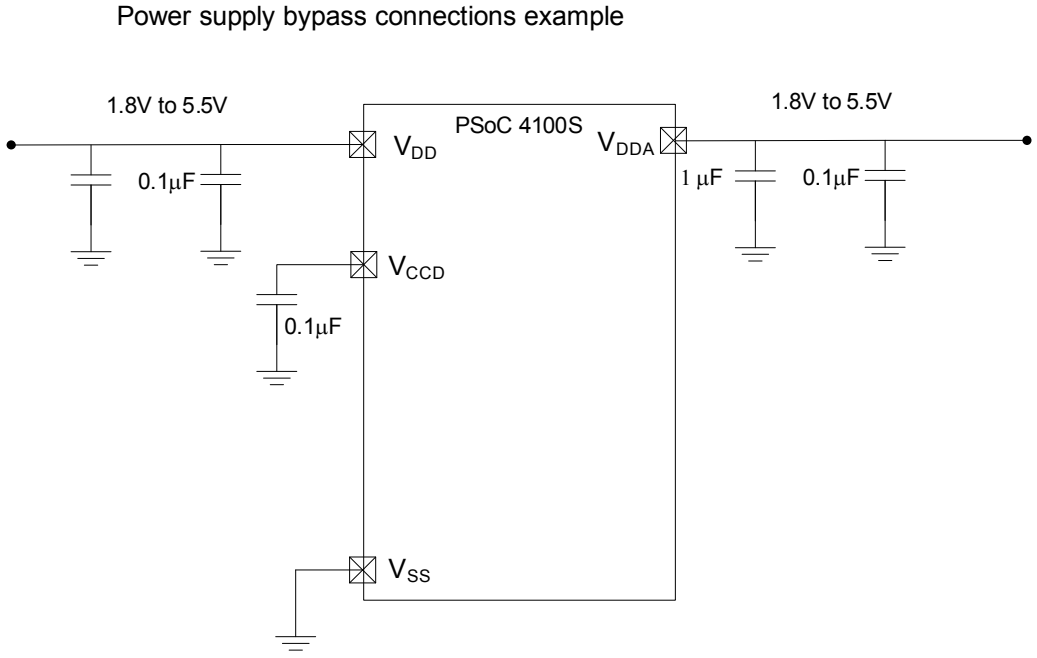
Mode 2: 1.8 V ±5% External Supply

In this mode, the PSoC 4100S is powered by an external power supply that must be within the range of 1.71 to 1.89 V; note that this range needs to include the power supply ripple too. In this mode, the VDD and VCCD pins are shorted together and bypassed. The internal regulator can be disabled in the firmware.

Bypass capacitors must be used from VDDD to ground. The typical practice for systems in this frequency range is to use a capacitor in the 1-µF range, in parallel with a smaller capacitor (0.1 µF, for example). Note that these are simply rules of thumb and that, for critical applications, the PCB layout, lead inductance, and the bypass capacitor parasitic should be simulated to design and obtain optimal bypassing.

An example of a bypass scheme is shown in the following diagram.

Figure 5. External Supply Range from 1.8 V to 5.5 V with Internal Regulator Active



Electrical Specifications

Absolute Maximum Ratings

Table 2. Absolute Maximum Ratings[1]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID1	V_{DDD_ABS}	Digital supply relative to V_{SS}	–0.5	–	6	V	–
SID2	V_{CCD_ABS}	Direct digital core voltage input relative to V_{SS}	–0.5	–	1.95		–
SID3	V_{GPIO_ABS}	GPIO voltage	–0.5	–	V_{DD}+0.5		–
SID4	I_{GPIO_ABS}	Maximum current per GPIO	–25	–	25	mA	–
SID5	$I_{GPIO\_injection}$	GPIO injection current, Max for V_{IH} > V_{DDD}, and Min for V_{IL} < V_{SS}	–0.5	–	0.5		Current injected per pin
BID44	ESD_HBM	Electrostatic discharge human body model	2200	–	–	V	–
BID45	ESD_CDM	Electrostatic discharge charged device model	500	–	–		–
BID46	LU	Pin current for latch-up	–140	–	140	mA	–

Device Level Specifications

All specifications are valid for –40 °C ≤ T_A ≤ 85 °C and T_J ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 3. DC Specifications

Typical values measured at V_{DD} = 3.3 V and 25 °C.

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID53	V_{DD}	Power supply input voltage	1.8	–	5.5	V	Internally regulated supply
SID255	V_{DD}	Power supply input voltage (V_{CCD} = V_{DDD} = V_{DDA})	1.71	–	1.89		Internally unregulated supply
SID54	V_{CCD}	Output voltage (for core logic)	–	1.8	–		–
SID55	C_{EFC}	External regulator voltage bypass	–	0.1	–	µF	X5R ceramic or better
SID56	C_{EXC}	Power supply bypass capacitor	–	1	–		X5R ceramic or better
Active Mode, V_{DD} = 1.8 V to 5.5 V. Typical values measured at VDD = 3.3 V and 25 °C.							
SID10	I_{DD5}	Execute from flash; CPU at 6 MHz	–	1.8	2.7	mA	Max is at 85 °C and 5.5 V
SID16	I_{DD8}	Execute from flash; CPU at 24 MHz	–	3.0	4.75		Max is at 85 °C and 5.5 V
SID19	I_{DD11}	Execute from flash; CPU at 48 MHz	–	5.4	6.85		Max is at 85 °C and 5.5 V

Note
1. Usage above the absolute maximum conditions listed in Table 2 may cause permanent damage to the device. Exposure to Absolute Maximum conditions for extended periods of time may affect device reliability. The Maximum Storage Temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below Absolute Maximum conditions but above normal operating conditions, the device may not operate to specification.

Table 3. DC Specifications *(continued)*

Typical values measured at V_{DD} = 3.3 V and 25 °C.

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
Sleep Mode, VDDD = 1.8 V to 5.5 V (Regulator on)							
SID22	IDD17	I^2C wakeup WDT, and Comparators on	–	1.7	2.2	mA	6 MHZ. Max is at 85 °C and 5.5 V.
SID25	IDD20	I^2C wakeup, WDT, and Comparators on.	–	2.2	2.5		12 MHZ. Max is at 85 °C and 5.5 V.
Sleep Mode, V_{DDD} = 1.71 V to 1.89 V (Regulator bypassed)							
SID28	IDD23	I^2C wakeup, WDT, and Comparators on	–	0.7	0.9	mA	6 MHZ. Max is at 85 °C and 5.5 V.
SID28A	IDD23A	I^2C wakeup, WDT, and Comparators on	–	1	1.2	mA	12 MHZ. Max is at 85 °C and 5.5 V.
Deep Sleep Mode, V_{DD} = 1.8 V to 3.6 V (Regulator on)							
SID31	I_{DD26}	I^2C wakeup and WDT on	–	2.5	60	µA	Max is at 3.6 V and 85 °C.
Deep Sleep Mode, V_{DD} = 3.6 V to 5.5 V (Regulator on)							
SID34	I_{DD29}	I^2C wakeup and WDT on	–	2.5	60	µA	Max is at 5.5 V and 85 °C.
Deep Sleep Mode, V_{DD} = V_{CCD} = 1.71 V to 1.89 V (Regulator bypassed)							
SID37	I_{DD32}	I^2C wakeup and WDT on	–	2.5	65	µA	Max is at 1.89 V and 85 °C.
XRES Current							
SID307	I_{DD_XR}	Supply current while XRES asserted	–	2	5	mA	–

Table 4. AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID48	F_{CPU}	CPU frequency	DC	–	48	MHz	$1.71 \le V_{DD} \le 5.5$
SID49[3]	T_{SLEEP}	Wakeup from Sleep mode	–	0	–	µs	
SID50[3]	$T_{DEEPSLEEP}$	Wakeup from Deep Sleep mode	–	35	–		

Note
2. Guaranteed by characterization.

GPIO

Table 5. GPIO DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID57	V_{IH}[3]	Input voltage high threshold	0.7 × V_{DDD}	–	–	V	CMOS Input
SID58	V_{IL}	Input voltage low threshold	–	–	0.3 × V_{DDD}		CMOS Input
SID241	V_{IH}[3]	LVTTL input, V_{DDD} < 2.7 V	0.7 × V_{DDD}	–	–		–
SID242	V_{IL}	LVTTL input, V_{DDD} < 2.7 V	–	–	0.3 × V_{DDD}		–
SID243	V_{IH}[3]	LVTTL input, V_{DDD} ≥ 2.7 V	2.0	–	–		–
SID244	V_{IL}	LVTTL input, V_{DDD} ≥ 2.7 V	–	–	0.8		–
SID59	V_{OH}	Output voltage high level	V_{DDD} –0.6	–	–		I_{OH} = 4 mA at 3 V V_{DDD}
SID60	V_{OH}	Output voltage high level	V_{DDD} –0.5	–	–		I_{OH} = 1 mA at 1.8 V V_{DDD}
SID61	V_{OL}	Output voltage low level	–	–	0.6		I_{OL} = 4 mA at 1.8 V V_{DDD}
SID62	V_{OL}	Output voltage low level	–	–	0.6		I_{OL} = 10 mA at 3 V V_{DDD}
SID62A	V_{OL}	Output voltage low level	–	–	0.4		I_{OL} = 3 mA at 3 V V_{DDD}
SID63	R_{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	–
SID64	$R_{PULLDOWN}$	Pull-down resistor	3.5	5.6	8.5		–
SID65	I_{IL}	Input leakage current (absolute value)	–	–	2	nA	25 °C, V_{DDD} = 3.0 V
SID66	C_{IN}	Input capacitance	–	–	7	pF	–
SID67[4]	V_{HYSTTL}	Input hysteresis LVTTL	25	40	–	mV	V_{DDD} ≥ 2.7 V
SID68[4]	$V_{HYSCMOS}$	Input hysteresis CMOS	0.05 × V_{DDD}	–	–		V_{DD} < 4.5 V
SID68A[4]	$V_{HYSCMOS5V5}$	Input hysteresis CMOS	200	–	–		V_{DD} > 4.5 V
SID69[4]	I_{DIODE}	Current through protection diode to V_{DD}/V_{SS}	–	–	100	µA	–
SID69A[4]	I_{TOT_GPIO}	Maximum total source or sink chip current	–	–	200	mA	–

Table 6. GPIO AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID70	T_{RISEF}	Rise time in fast strong mode	2	–	12	ns	3.3 V V_{DDD}, Cload = 25 pF
SID71	T_{FALLF}	Fall time in fast strong mode	2	–	12		3.3 V V_{DDD}, Cload = 25 pF
SID72	T_{RISES}	Rise time in slow strong mode	10	–	60	–	3.3 V V_{DDD}, Cload = 25 pF

Notes
3. V_{IH} must not exceed V_{DDD} + 0.2 V.
4. Guaranteed by characterization.

Table 6. GPIO AC Specifications

(Guaranteed by Characterization) *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID73	T_{FALLS}	Fall time in slow strong mode	10	–	60	–	3.3 V V_{DDD}, Cload = 25 pF
SID74	$F_{GPIOUT1}$	GPIO F_{OUT}; 3.3 V ≤ V_{DDD} ≤ 5.5 V Fast strong mode	–	–	33	MHz	90/10%, 25 pF load, 60/40 duty cycle
SID75	$F_{GPIOUT2}$	GPIO F_{OUT}; 1.71 V≤ V_{DDD}≤ 3.3 V Fast strong mode	–	–	16.7		90/10%, 25 pF load, 60/40 duty cycle
SID76	$F_{GPIOUT3}$	GPIO F_{OUT}; 3.3 V ≤ V_{DDD} ≤ 5.5 V Slow strong mode	–	–	7		90/10%, 25 pF load, 60/40 duty cycle
SID245	$F_{GPIOUT4}$	GPIO F_{OUT}; 1.71 V ≤ V_{DDD} ≤ 3.3 V Slow strong mode.	–	–	3.5		90/10%, 25 pF load, 60/40 duty cycle
SID246	F_{GPIOIN}	GPIO input operating frequency; 1.71 V ≤ V_{DDD} ≤ 5.5 V	–	–	48		90/10% V_{IO}

XRES

Table 7. XRES DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID77	V_{IH}	Input voltage high threshold	0.7 × V_{DDD}	–	–	V	CMOS Input
SID78	V_{IL}	Input voltage low threshold	–	–	0.3 × V_{DDD}		
SID79	R_{PULLUP}	Pull-up resistor	–	60	–	kΩ	–
SID80	C_{IN}	Input capacitance	–	–	7	pF	–
SID81[5]	$V_{HYSXRES}$	Input voltage hysteresis	–	100	–	mV	Typical hysteresis is 200 mV for V_{DD} > 4.5 V
SID82	I_{DIODE}	Current through protection diode to V_{DD}/V_{SS}	–	–	100	µA	

Table 8. XRES AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID83[5]	$T_{RESETWIDTH}$	Reset pulse width	1	–	–	µs	–
BID194[5]	$T_{RESETWAKE}$	Wake-up time from reset release	–	–	2.7	ms	–

Note
5. Guaranteed by characterization.

Table 9. CTBm Opamp Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
		General opamp specs for both internal and external modes					
SID281	V_{IN}	Charge-pump on, V_{DDA} = 2.7 V	–0.05	–	V_{DDA}-0.2	V	–
SID282	V_{CM}	Charge-pump on, V_{DDA} = 2.7 V	–0.05	–	V_{DDA}-0.2		–
	V_{OUT}	V_{DDA} = 2.7 V					
SID283	V_{OUT_1}	power=hi, Iload=10 mA	0.5	–	V_{DDA} -0.5	V	–
SID284	V_{OUT_2}	power=hi, Iload=1 mA	0.2	–	V_{DDA} -0.2		–
SID285	V_{OUT_3}	power=med, Iload=1 mA	0.2	–	V_{DDA} -0.2		–
SID286	V_{OUT_4}	power=lo, Iload=0.1 mA	0.2	–	V_{DDA} -0.2		–
SID288	V_{OS_TR}	Offset voltage, trimmed	–1.0	±0.5	1.0	mV	High mode, input 0 V to V_{DDA}-0.2 V
SID288A	V_{OS_TR}	Offset voltage, trimmed	–	±1	–		Medium mode, input 0 V to V_{DDA}-0.2 V
SID288B	V_{OS_TR}	Offset voltage, trimmed	–	±2	–		Low mode, input 0 V to V_{DDA}-0.2 V
SID290	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–10	±3	10	µV/C	High mode
SID290A	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–	µV/C	Medium mode
SID290B	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–		Low mode
SID291	CMRR	DC	70	80	–	dB	Input is 0 V to V_{DDA}-0.2 V, Output is 0.2 V to V_{DDA}-0.2 V
SID292	PSRR	At 1 kHz, 10-mV ripple	70	85	–		V_{DDD} = 3.6 V, high-power mode, input is 0.2 V to V_{DDA}-0.2 V
	Noise						
SID294	VN2	Input-referred, 1 kHz, power=Hi	–	72	–	nV/rtHz	3
SID295	VN3	Input-referred, 10 kHz, power=Hi	–	28	–		Input and output are at 0.2 V to V_{DDA}-0.2 V
SID296	VN4	Input-referred, 100 kHz, power=Hi	–	15	–		Input and output are at 0.2 V to V_{DDA}-0.2 V
SID297	C_{LOAD}	Stable up to max. load. Performance specs at 50 pF.	–	–	125	pF	–
SID298	SLEW_RATE	Cload = 50 pF, Power = High, V_{DDA} = 2.7 V	6	–	–	V/µs	–

Table 13. SAR Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID99	A_OFFSET	Input offset voltage	–	–	2	mV	Measured with 1-V reference
SID100	A_ISAR	Current consumption	–	–	1	mA	
SID101	A_VINS	Input voltage range - single ended	V_{SS}	–	V_{DDA}	V	
SID102	A_VIND	Input voltage range - differential[	V_{SS}	–	V_{DDA}	V	
SID103	A_INRES	Input resistance	–	–	2.2	KΩ	
SID104	A_INCAP	Input capacitance	–	–	10	pF	
SID260	VREFSAR	Trimmed internal reference to SAR	–	–	TBD	V	
SAR ADC AC Specifications							
SID106	A_PSRR	Power supply rejection ratio	70	–	–	dB	
SID107	A_CMRR	Common mode rejection ratio	66	–	–	dB	Measured at 1 V
SID108	A_SAMP	Sample rate	–	–	1	Msps	
SID109	A_SNR	Signal-to-noise and distortion ratio (SINAD)	65	–	–	dB	F_{IN} = 10 kHz
SID110	A_BW	Input bandwidth without aliasing	–	–	A_samp/2	kHz	
SID111	A_INL	Integral non linearity. V_{DD} = 1.71 to 5.5, 1 Msps	–1.7	–	2	LSB	V_{REF} = 1 to V_{DD}
SID111A	A_INL	Integral non linearity. V_{DDD} = 1.71 to 3.6, 1 Msps	–1.5	–	1.7	LSB	V_{REF} = 1.71 to V_{DD}
SID111B	A_INL	Integral non linearity. V_{DD} = 1.71 to 5.5, 500 ksps	–1.5	–	1.7	LSB	V_{REF} = 1 to V_{DD}
SID112	A_DNL	Differential non linearity. V_{DD} = 1.71 to 5.5, 1 Msps	–1	_	2.2	LSB	V_{REF} = 1 to V_{DD}
SID112A	A_DNL	Differential non linearity. V_{DD} = 1.71 to 3.6, 1 Msps	–1	_	2	LSB	V_{REF} = 1.71 to V_{DD}
SID112B	A_DNL	Differential non linearity. V_{DD} = 1.71 to 5.5, 500 ksps	–1	_	2.2	LSB	V_{REF} = 1 to V_{DD}
SID113	A_THD	Total harmonic distortion	–	–	–65	dB	Fin = 10 kHz
SID261	FSARINTREF	SAR operating speed without external ref. bypass	_	_	100	ksps	12-bit resolution

CSD

Table 14. CSD and IDAC Specifications

SPEC ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SYS.PER#3	VDD_RIPPLE	Max allowed ripple on power supply, DC to 10 MHz	–	–	±50	mV	V_{DD} > 2 V (with ripple), 25 °C T_A, Sensitivity = 0.1 pF
SYS.PER#16	VDD_RIPPLE_1.8	Max allowed ripple on power supply, DC to 10 MHz	–	–	±25	mV	V_{DD} > 1.75V (with ripple), 25 °C T_A, Parasitic Capacitance (C_P) < 20 pF, Sensitivity ≥ 0.4 pF
SID.CSD.BLK	ICSD	Maximum block current	–	–	4000	µA	Maximum block current for both IDACs in dynamic (switching) mode including comparators, buffer, and reference generator.
SID.CSD#15	V_{REF}	Voltage reference for CSD and Comparator	0.6	1.2	V_{DDA} - 0.6	V	V_{DDA} - 0.06 or 4.4, whichever is lower
SID.CSD#15A	VREF_EXT	External Voltage reference for CSD and Comparator	0.6		V_{DDA} - 0.6	V	V_{DDA} - 0.06 or 4.4, whichever is lower
SID.CSD#16	IDAC1IDD	IDAC1 (7-bits) block current	–	–	1750	µA	
SID.CSD#17	IDAC2IDD	IDAC2 (7-bits) block current	–	–	1750	µA	
SID308	VCSD	Voltage range of operation	1.71	–	5.5	V	1.8 V ±5% or 1.8 V to 5.5 V
SID308A	VCOMPIDAC	Voltage compliance range of IDAC	0.6	–	V_{DDA} –0.6	V	V_{DDA} - 0.06 or 4.4, whichever is lower
SID309	IDAC1DNL	DNL	–1	–	1	LSB	
SID310	IDAC1INL	INL	–2	–	2	LSB	INL is ±5.5 LSB for V_{DDA} < 2 V
SID311	IDAC2DNL	DNL	–1	–	1	LSB	
SID312	IDAC2INL	INL	–2	–	2	LSB	INL is ±5.5 LSB for V_{DDA} < 2 V
SID313	SNR	Ratio of counts of finger to noise. Guaranteed by characterization	5	–	–	Ratio	Capacitance range of 5 to 35 pF, 0.1-pF sensitivity. All use cases. V_{DDA} > 2 V.
SID314	IDAC1CRT1	Output current of IDAC1 (7 bits) in low range	4.2	–	5.4	µA	LSB = 37.5-nA typ.
SID314A	IDAC1CRT2	Output current of IDAC1(7 bits) in medium range	34	–	41	µA	LSB = 300-nA typ.
SID314B	IDAC1CRT3	Output current of IDAC1(7 bits) in high range	275	–	330	µA	LSB = 2.4-µA typ.
SID314C	IDAC1CRT12	Output current of IDAC1 (7 bits) in low range, 2X mode	8	–	10.5	µA	LSB = 75-nA typ.
SID314D	IDAC1CRT22	Output current of IDAC1(7 bits) in medium range, 2X mode	69	–	82	µA	LSB = 600-nA typ.
SID314E	IDAC1CRT32	Output current of IDAC1(7 bits) in high range, 2X mode	540	–	660	µA	LSB = 4.8-µA typ.
SID315	IDAC2CRT1	Output current of IDAC2 (7 bits) in low range	4.2	–	5.4	µA	LSB = 37.5-nA typ.
SID315A	IDAC2CRT2	Output current of IDAC2 (7 bits) in medium range	34	–	41	µA	LSB = 300-nA typ.
SID315B	IDAC2CRT3	Output current of IDAC2 (7 bits) in high range	275	–	330	µA	LSB = 2.4-µA typ.
SID315C	IDAC2CRT12	Output current of IDAC2 (7 bits) in low range, 2X mode	8	–	10.5	µA	LSB = 75-nA typ.
SID315D	IDAC2CRT22	Output current of IDAC2(7 bits) in medium range, 2X mode	69	–	82	µA	LSB = 600-nA typ.
SID315E	IDAC2CRT32	Output current of IDAC2(7 bits) in high range, 2X mode	540	–	660	µA	LSB = 4.8-µA typ.
SID315F	IDAC3CRT13	Output current of IDAC in 8-bit mode in low range	8	–	10.5	µA	LSB = 37.5-nA typ.

Table 15. 10-bit CapSense ADC Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SIDA109	A_SND	Signal-to-noise and Distortion ratio (SINAD)	–	61	–	dB	With 10-Hz input sine wave, external 2.4-V reference, V_{REF} (2.4 V) mode
SIDA110	A_BW	Input bandwidth without aliasing	–	–	22.4	KHz	8-bit resolution
SIDA111	A_INL	Integral Non Linearity. 1 ksps	–	–	2	LSB	V_{REF} = 2.4 V or greater
SIDA112	A_DNL	Differential Non Linearity. 1 ksps	–	–	1	LSB	

Digital Peripherals

Timer Counter Pulse-Width Modulator (TCPWM)

Table 16. TCPWM Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.TCPWM.1	ITCPWM1	Block current consumption at 3 MHz	–	–	45	µA	All modes (TCPWM)
SID.TCPWM.2	ITCPWM2	Block current consumption at 12 MHz	–	–	155		All modes (TCPWM)
SID.TCPWM.2A	ITCPWM3	Block current consumption at 48 MHz	–	–	650		All modes (TCPWM)
SID.TCPWM.3	$TCPWM_{FREQ}$	Operating frequency	–	–	Fc	MHz	Fc max = CLK_SYS Maximum = 48 MHz
SID.TCPWM.4	$TPWM_{ENEXT}$	Input trigger pulse width	2/Fc	–	–	ns	For all trigger events[7]
SID.TCPWM.5	$TPWM_{EXT}$	Output trigger pulse widths	2/Fc	–	–		Minimum possible width of Overflow, Underflow, and CC (Counter equals Compare value) outputs
SID.TCPWM.5A	TC_{RES}	Resolution of counter	1/Fc	–	–		Minimum time between successive counts
SID.TCPWM.5B	PWM_{RES}	PWM resolution	1/Fc	–	–		Minimum pulse width of PWM Output
SID.TCPWM.5C	Q_{RES}	Quadrature inputs resolution	1/Fc	–	–		Minimum pulse width between Quadrature phase inputs

I^2C

Table 17. Fixed I^2C DC Specifications[8]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID149	I_{I2C1}	Block current consumption at 100 kHz	–	–	50	µA	–
SID150	I_{I2C2}	Block current consumption at 400 kHz	–	–	135		–
SID151	I_{I2C3}	Block current consumption at 1 Mbps	–	–	310		–
SID152	I_{I2C4}	I^2C enabled in Deep Sleep mode	–	–	1.4		

Table 18. Fixed I^2C AC Specifications[8]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID153	F_{I2C1}	Bit rate	–	–	1	Msps	–

Notes
7. Trigger events can be Stop, Start, Reload, Count, Capture, or Kill depending on which mode of operation is selected.

Note
8. Guaranteed by characterization.

Table 21. UART DC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID160	I_{UART1}	Block current consumption at 100 Kbps	–	–	55	µA	–
SID161	I_{UART2}	Block current consumption at 1000 Kbps	–	–	312	µA	–

Table 22. UART AC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID162	F_{UART}	Bit rate	–	–	1	Mbps	–

Table 23. LCD Direct Drive DC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID154	I_{LCDLOW}	Operating current in low power mode	–	5	–	µA	16 × 4 small segment disp. at 50 Hz
SID155	C_{LCDCAP}	LCD capacitance per segment/common driver	–	500	5000	pF	–
SID156	LCD_{OFFSET}	Long-term segment offset	–	20	–	mV	–
SID157	I_{LCDOP1}	LCD system operating current Vbias = 5 V	–	2	–	mA	32 × 4 segments. 50 Hz. 25 °C
SID158	I_{LCDOP2}	LCD system operating current Vbias = 3.3 V	–	2	–		32 × 4 segments. 50 Hz. 25 °C

Table 24. LCD Direct Drive AC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID159	F_{LCD}	LCD frame rate	10	50	150	Hz	–

Note
9. Guaranteed by characterization.

Memory

Table 25. Flash DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID173	V_{PE}	Erase and program voltage	1.71	–	5.5	V	–

Table 26. Flash AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID174	$T_{ROWWRITE}$[10]	Row (block) write time (erase and program)	–	–	20	ms	Row (block) = 128 bytes
SID175	$T_{ROWERASE}$[10]	Row erase time	–	–	16		–
SID176	$T_{ROWPROGRAM}$[10]	Row program time after erase	–	–	4		–
SID178	$T_{BULKERASE}$[10]	Bulk erase time (64 KB)	–	–	35		–
SID180[11]	$T_{DEVPROG}$[10]	Total device program time	–	–	7	Seconds	–
SID181[11]	F_{END}	Flash endurance	100 K	–	–	Cycles	–
SID182[11]	F_{RET}	Flash retention. $T_A \leq 55$ °C, 100 K P/E cycles	20	–	–	Years	–
SID182A[11]	–	Flash retention. $T_A \leq 85$ °C, 10 K P/E cycles	10	–	–		–
SID256	TWS48	Number of Wait states at 48 MHz	2	–	–		CPU execution from Flash
SID257	TWS24	Number of Wait states at 24 MHz	1	–	–		CPU execution from Flash

System Resources

Power-on Reset (POR)

Table 27. Power On Reset (PRES)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.CLK#6	SR_POWER_UP	Power supply slew rate	1	–	67	V/ms	At power-up
SID185[11]	$V_{RISEIPOR}$	Rising trip voltage	0.80	–	1.5	V	–
SID186[11]	$V_{FALLIPOR}$	Falling trip voltage	0.70	–	1.4		–

Table 28. Brown-out Detect (BOD) for V_{CCD}

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID190[11]	$V_{FALLPPOR}$	BOD trip voltage in active and sleep modes	1.48	–	1.62	V	–
SID192[11]	$V_{FALLDPSLP}$	BOD trip voltage in Deep Sleep	1.11	–	1.5		–

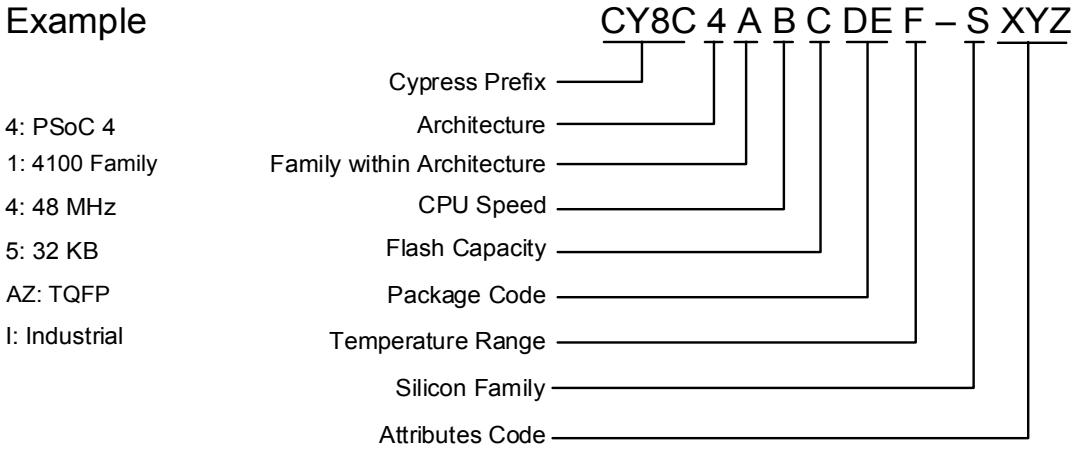
Notes
10. It can take as much as 20 milliseconds to write to Flash. During this time the device should not be Reset, or Flash operations will be interrupted and cannot be relied on to have completed. Reset sources include the XRES pin, software resets, CPU lockup states and privilege violations, improper power supply levels, and watchdogs. Make certain that these are not inadvertently activated.
11. Guaranteed by characterization.

The nomenclature used in the preceding table is based on the following part numbering convention:

Field	Description	Values	Meaning
CY8C	Cypress Prefix		
4	Architecture	4	PSoC 4
A	Family	1	4100 Family
B	CPU Speed	2	24 MHz
		4	48 MHz
C	Flash Capacity	4	16 KB
		5	32 KB
		6	64 KB
		7	128 KB
DE	Package Code	AX	TQFP (0.8mm pitch)
		AZ	TQFP (0.5mm pitch)
		LQ	QFN
		PV	SSOP
		FN	CSP
F	Temperature Range	I	Industrial
S	Silicon Family	S	PSoC 4A-S1, PSoC 4A-S2
		M	PSoC 4A-M
		L	PSoC 4A-L
		BL	PSoC 4A-BLE
XYZ	Attributes Code	000-999	Code of feature set in the specific family

The following is an example of a part number:

Example



Packaging

The PSoC 4100S will be offered in 48-pin TQFP, 44-pin TQFP, 40-pin QFN, 32-pin QFN, and 35-ball WLCSP packages. Package dimensions and Cypress drawing numbers are in the following table.

Table 38. Package List

Spec ID#	Package	Description	Package Dwg
BID20	48-pin TQFP	7 × 7 × 1.4-mm height with 0.5-mm pitch	51-85135
BID20A	44-pin TQFP	10 × 10 × 1.6-mm height with 0.8-mm pitch	51-85064
BID27	40-pin QFN	6 × 6 × 0.6-mm height with 0.5-mm pitch	001-80659
BID34A	32-pin QFN	5 × 5 × 0.6-mm height with 0.5-mm pitch	001-42168
BID34D	35-ball WLCSP	2.6 × 2.1 × 0.48-mm height with 0.35-mm pitch	002-09958

Table 39. Package Thermal Characteristics

Parameter	Description	Package	Min	Typ	Max	Units
T_A	Operating Ambient temperature		–40	25	85	°C
T_J	Operating junction temperature		–40	–	100	°C
T_{JA}	Package θ_{JA}	48-pin TQFP	–	74.8	–	°C/Watt
T_{JC}	Package θ_{JC}	48-pin TQFP	–	35.7	–	°C/Watt
T_{JA}	Package θ_{JA}	44-pin TQFP	–	57.2	–	°C/Watt
T_{JC}	Package θ_{JC}	44-pin TQFP	–	17.5	–	°C/Watt
T_{JA}	Package θ_{JA}	40-pin QFN	–	17.8	–	°C/Watt
T_{JC}	Package θ_{JC}	40-pin QFN	–	2.8	–	°C/Watt
T_{JA}	Package θ_{JA}	32-pin QFN	–	19.9	–	°C/Watt
T_{JC}	Package θ_{JC}	32-pin QFN	–	4.3	–	°C/Watt
T_{JA}	Package θ_{JA}	35-ball WLCSP	–	43	–	°C/Watt
T_{JC}	Package θ_{JC}	35-ball WLCSP	–	0.3	–	°C/Watt

Table 40. Solder Reflow Peak Temperature

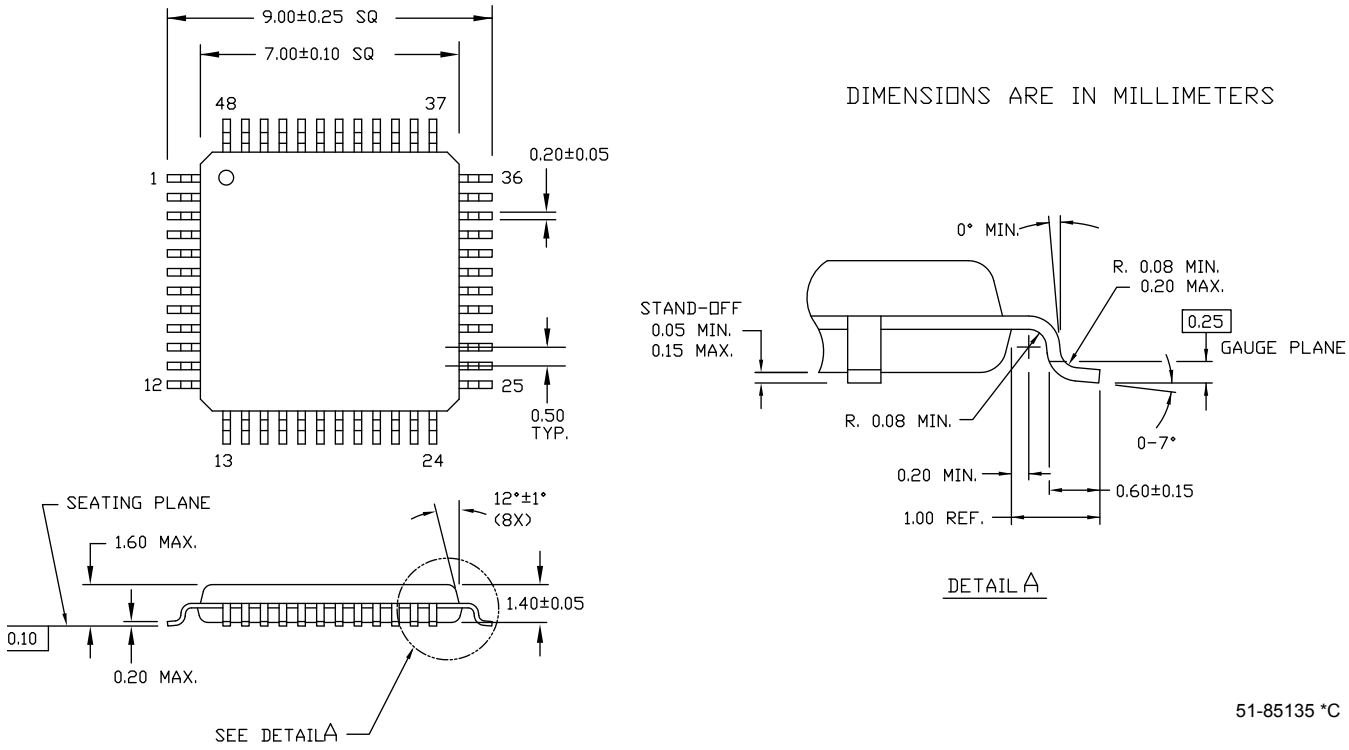
Package	Maximum Peak Temperature	Maximum Time at Peak Temperature
All	260 °C	30 seconds

Table 41. Package Moisture Sensitivity Level (MSL), IPC/JEDEC J-STD-020

Package	MSL
All except WLCSP	MSL 3
35-ball WLCSP	MSL 1

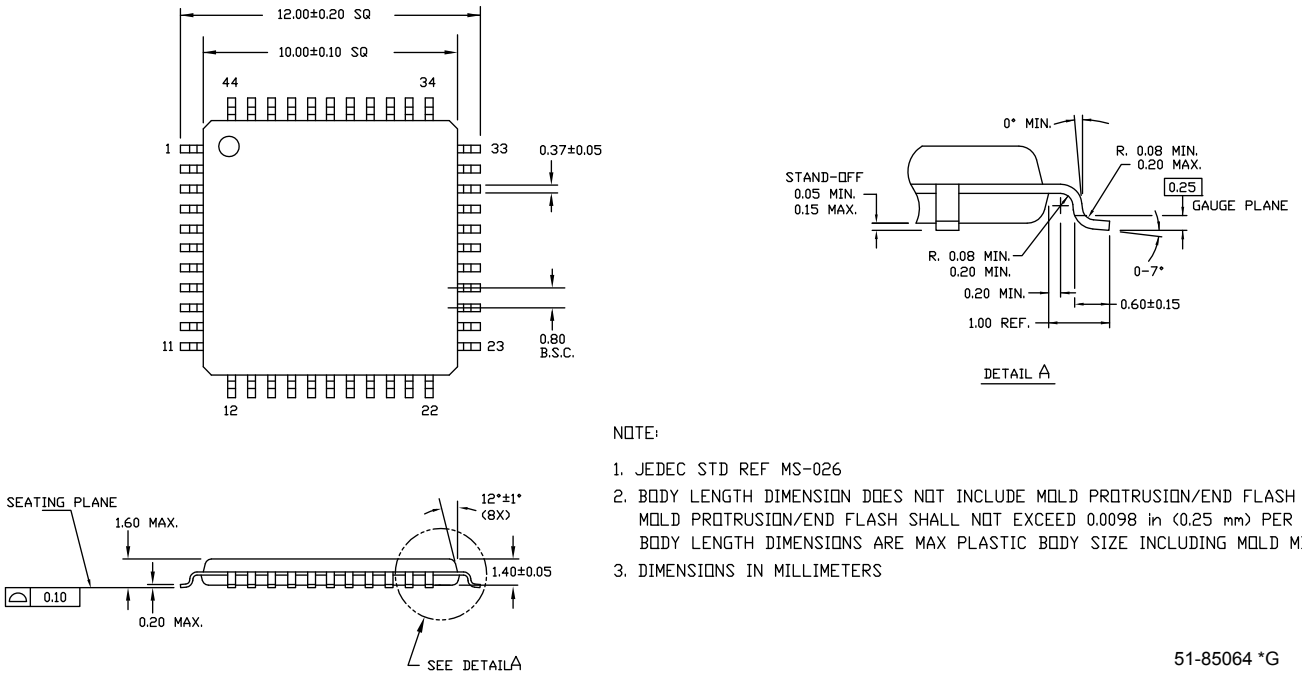
Package Diagrams

Figure 6. 48-pin TQFP Package Outline



51-85135 *C

Figure 7. 44-pin TQFP Package Outline

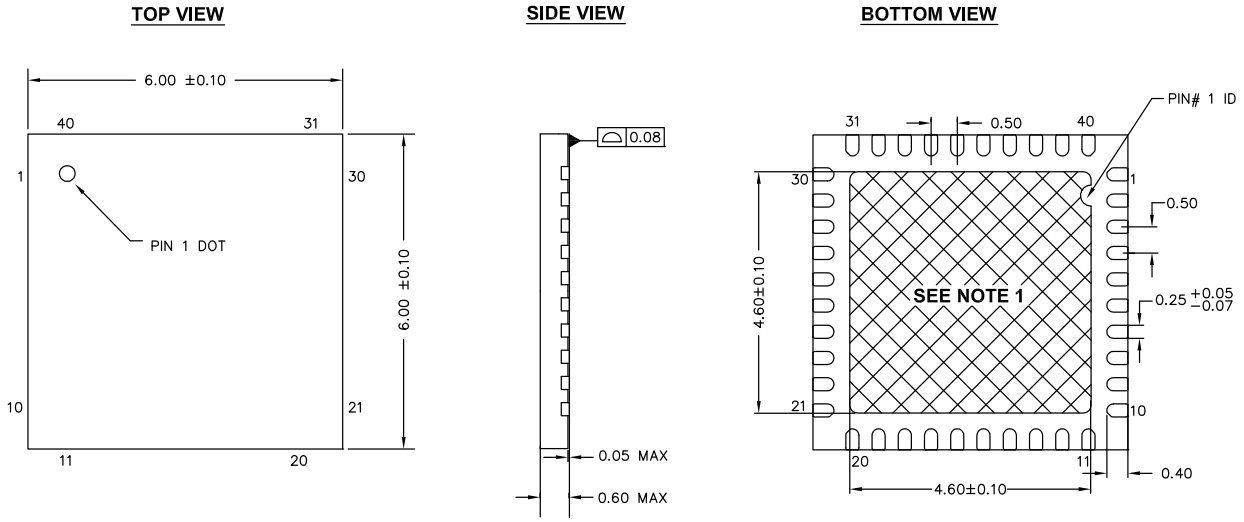


NOTE:

1. JEDEC STD REF MS-026
2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH
   MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.0098 in (0.25 mm) PER SIDE
   BODY LENGTH DIMENSIONS ARE MAX PLASTIC BODY SIZE INCLUDING MOLD MISMATCH
3. DIMENSIONS IN MILLIMETERS

51-85064 *G

Figure 8. 40-pin QFN Package Outline

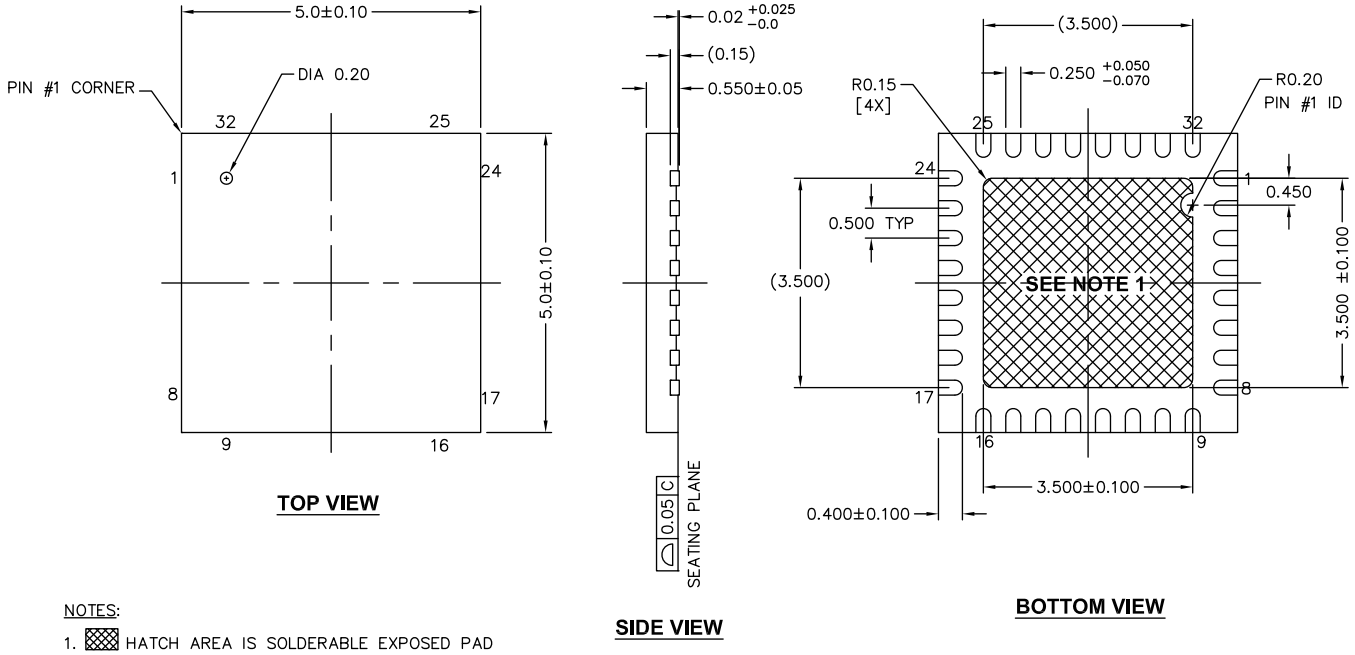


NOTES:

1. HATCH AREA IS SOLDERABLE EXPOSED PAD
2. REFERENCE JEDEC # MO-248
3. PACKAGE WEIGHT: 68 ±2 mg
4. ALL DIMENSIONS ARE IN MILLIMETERS

001-80659 *A

Figure 9. 32-pin QFN Package Outline



NOTES:

1. HATCH AREA IS SOLDERABLE EXPOSED PAD
2. BASED ON REF JEDEC # MO−248
3. PACKAGE WEIGHT: 0.0388g
4. DIMENSIONS ARE IN MILLIMETERS

001-42168 *E

Document Conventions

Units of Measure

Table 43. Units of Measure

Symbol	Unit of Measure
°C	degrees Celsius
dB	decibel
fF	femto farad
Hz	hertz
KB	1024 bytes
kbps	kilobits per second
Khr	kilohour
kHz	kilohertz
kΩ	kilo ohm
ksps	kilosamples per second
LSB	least significant bit
Mbps	megabits per second
MHz	megahertz
MΩ	mega-ohm
Msps	megasamples per second
µA	microampere
µF	microfarad
µH	microhenry
µs	microsecond
µV	microvolt
µW	microwatt
mA	milliampere
ms	millisecond
mV	millivolt
nA	nanoampere
ns	nanosecond
nV	nanovolt
Ω	ohm
pF	picofarad
ppm	parts per million
ps	picosecond
s	second
sps	samples per second
sqrtHz	square root of hertz
V	volt

Revision History

Description Title: PSoC® 4: PSoC 4100S Family Datasheet Programmable System-on-Chip (PSoC) Document Number: 002-00122				
Revision	**ECN**	**Orig. of Change**	**Submission Date**	**Description of Change**
**	4883809	WKA	08/28/2015	New datasheet
*A	4992376	WKA	10/30/2015	Updated Pinouts. Added V_{DDD} ≥ 2.2V at –40 °C under Conditions for specs SID247A, SID90, SID92. Updated Table 15. Updated Ordering Information.
*B	5037826	SLAN	12/08/2015	Changed datasheet status to Preliminary
*C	5060691	WKA	12/22/2015	Updated SCBs from 2 to 3. Updated SRAM size to 8 KB. Changed WLCSP package to 35-ball WLCSP. Updated Pin List and Alternate Pin Functions. Updated Ordering Information.
*D	5139206	WKA	02/16/2016	Added Errata. Added 35 WLCSP package details. Updated theta J_A and J_C values for all packages. Updated copyright information at the end of the document.
*E	5173961	WKA	03/15/2016	Updated values for SID79, BID194. SID175, and SID176. Updated CSD and IDAC Specifications. Updated 10-bit CapSense ADC Specifications.
*F	5330930	WKA	07/27/2016	Updated CSD and IDAC Specifications. Updated 10-bit CapSense ADC Specifications. Removed errata.
*G	5473409	WKA	10/13/2016	Added 44 TQFP pin and package details.
*H	5561833	WKA	01/09/2017	Updated Figure 3. Changed PRGIO references to Smart I/O. Updated DC Specifications. Updated Ordering Information.